

# **Re-entrant antiferromagnetism in the exchange-coupled IrMn/NiFe system**

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# Objective

Description of the dynamic magnetic behavior of the antiferromagnet in exchange-coupled FM/ AFM **NiFe/IrMn bilayers**

## Re-entrant antiferromagnetism

- From the continuous NiFe/IrMn film to **dot arrays**: spatial confinement and exchange coupling mechanism

We exploit the exchange coupling with a soft FM as a tool to gain an insight into the magnetic properties of the AFM

We study the magnetic properties of the AFM phase to gain an insight into the exchange coupling mechanism (*exchange bias effect*)



# NiFe/IrMn film

Si / Cu[5 nm] / Py[5 nm] / IrMn[6 nm] / Cu [5 nm]

Py: Ni<sub>80</sub>Fe<sub>20</sub>

IrMn: Ir<sub>25</sub>Mn<sub>75</sub>

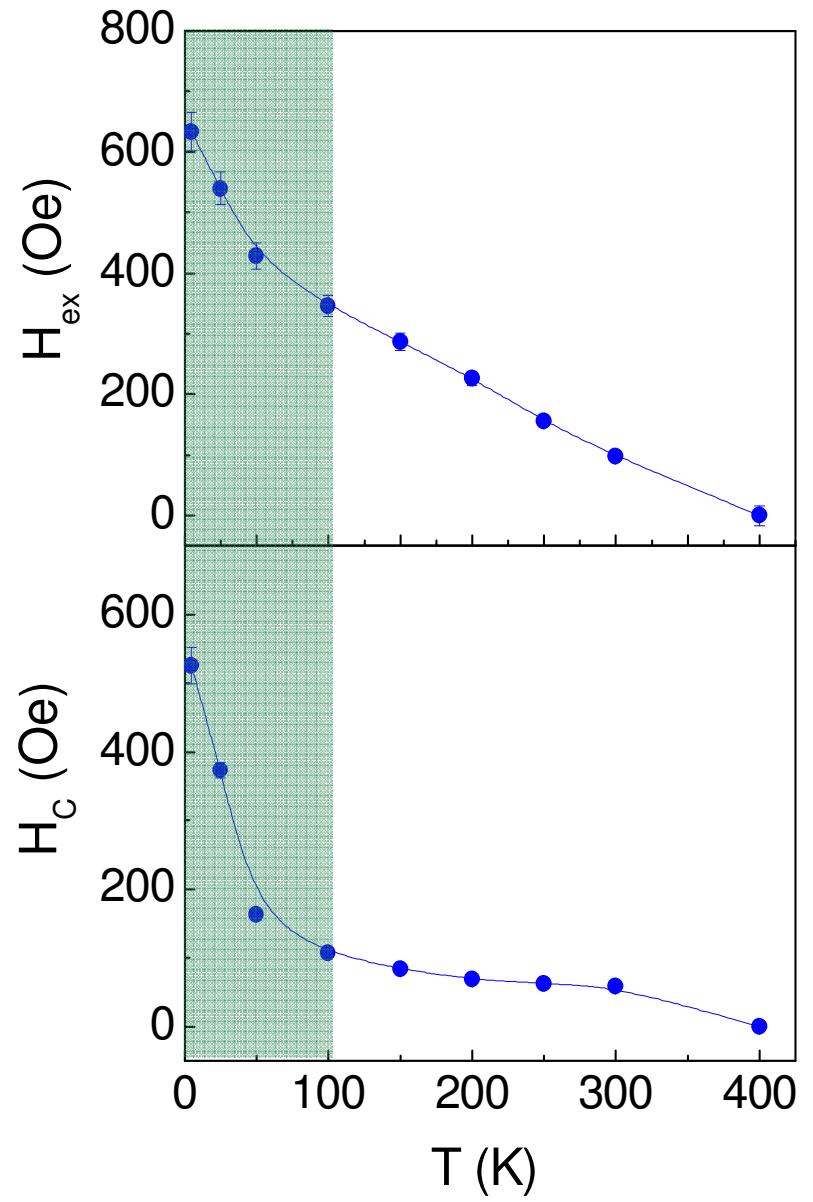
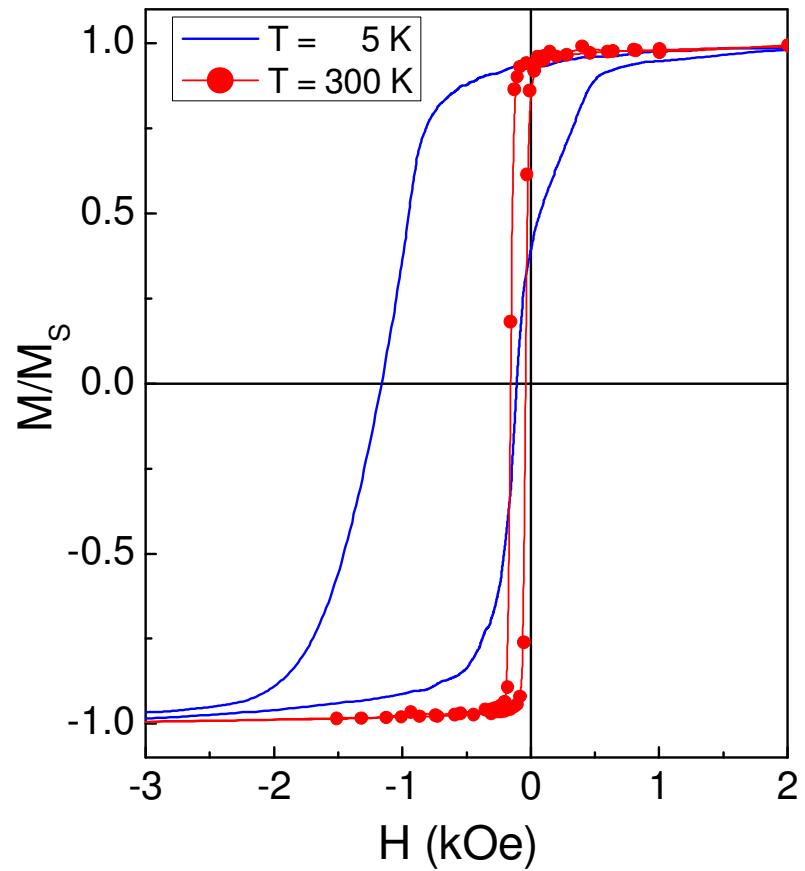
*Reference film: Si / Cu[5 nm] / Py[5 nm] / Cu [5 nm]*

Deposition by **dc-magnetron sputtering**

Ar atmosphere, deposition rate  $\simeq 0.2$  nm/s

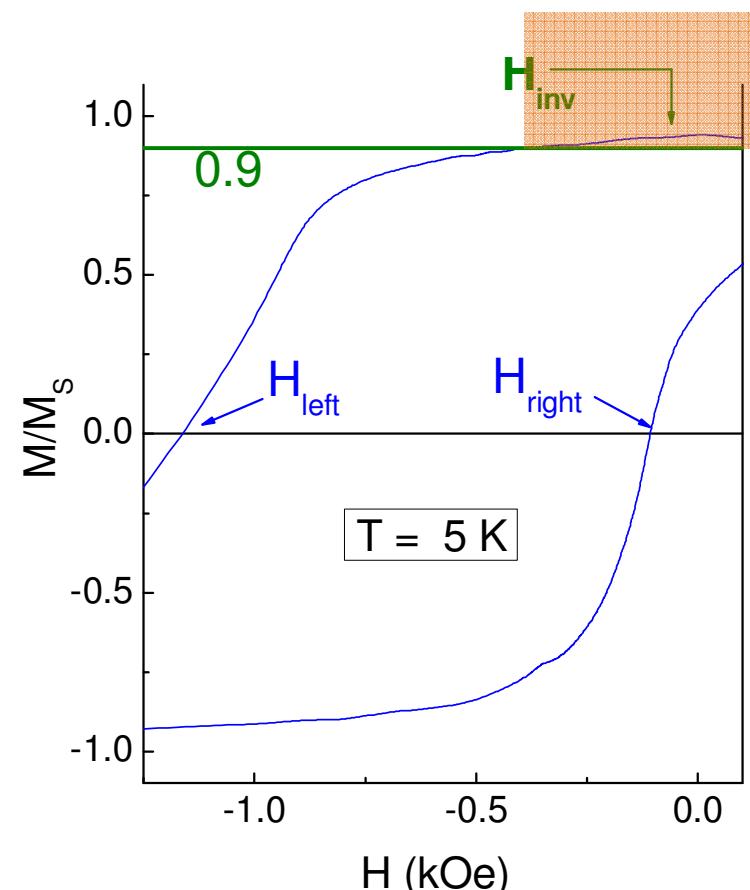
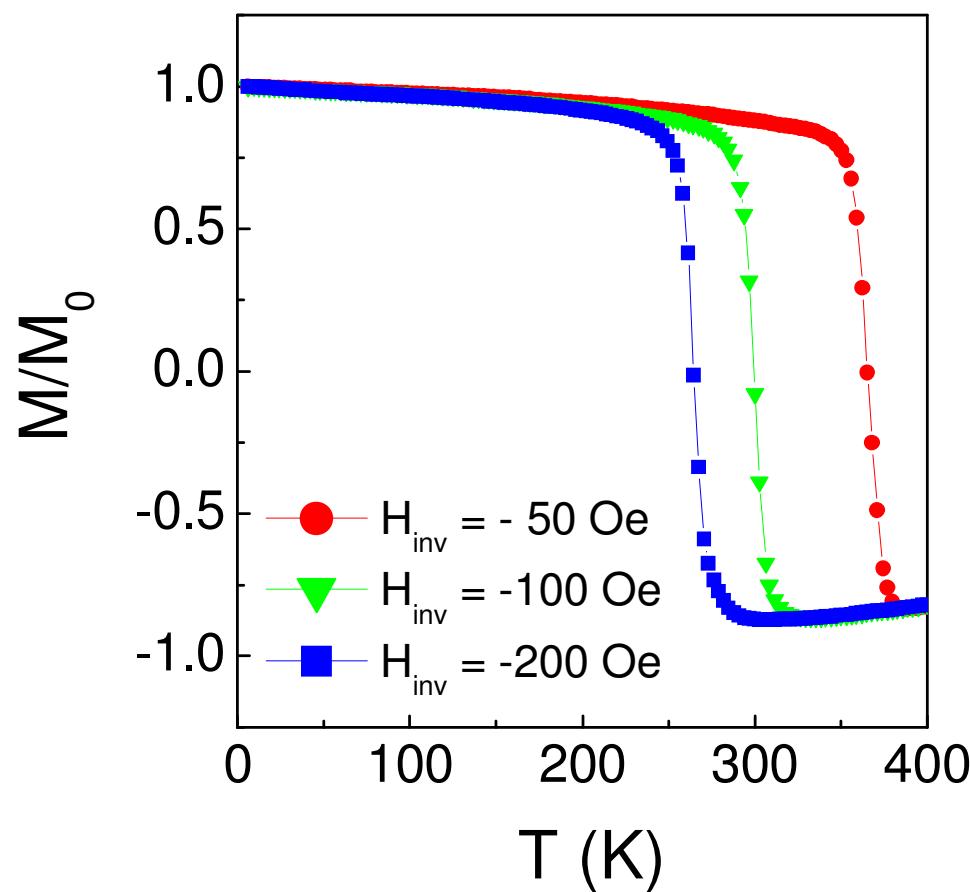
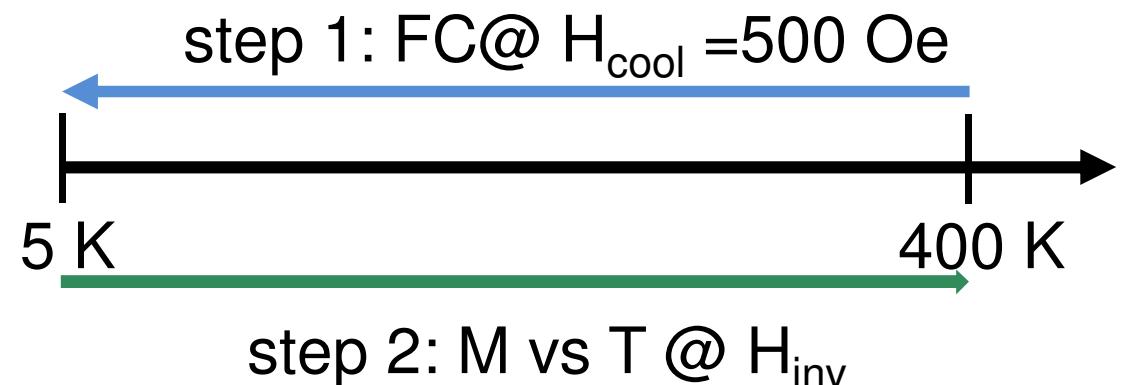
**H<sub>dep</sub> = 400 Oe**

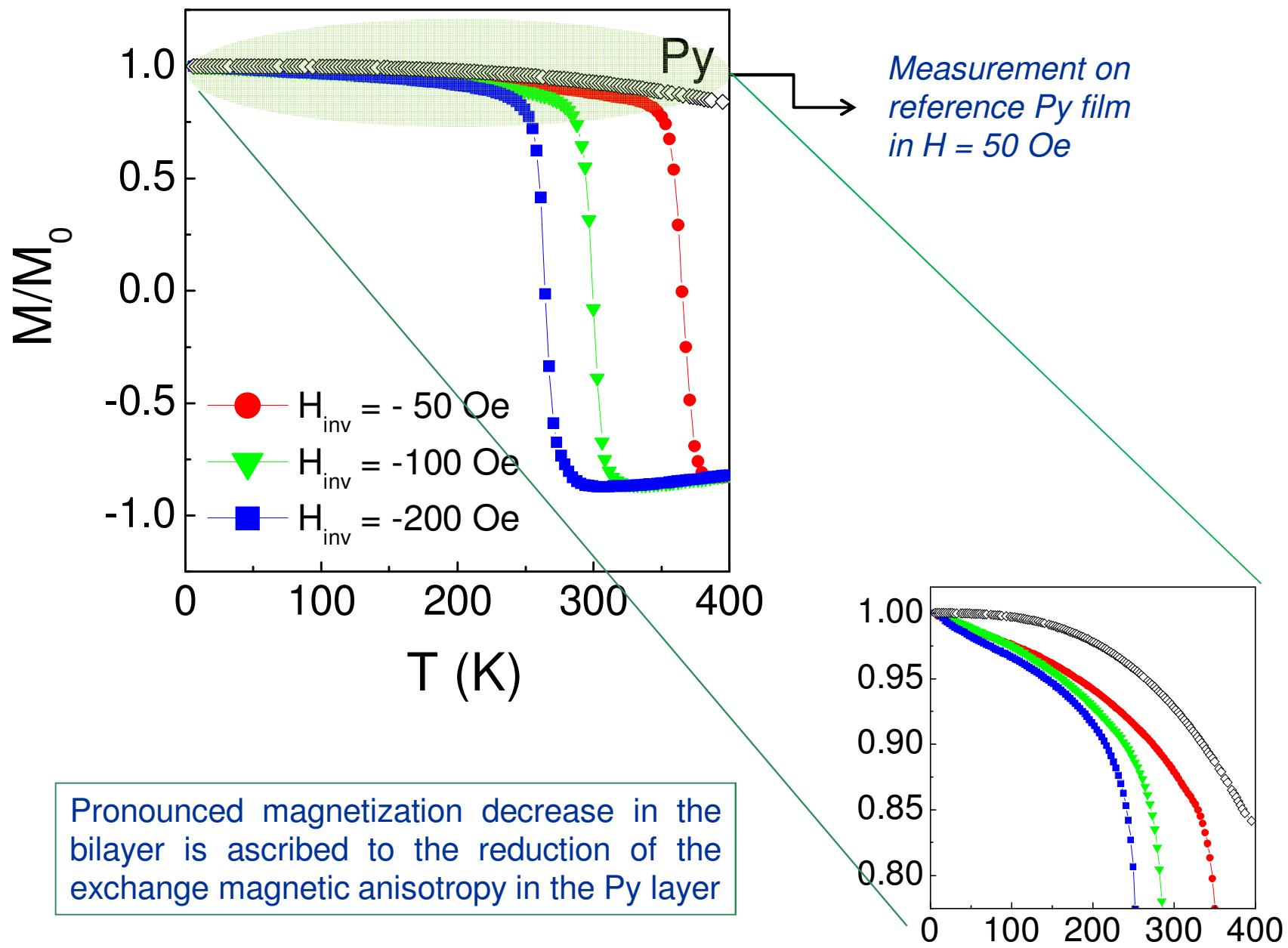
## Hysteresis loops (5-400 K temperature range)

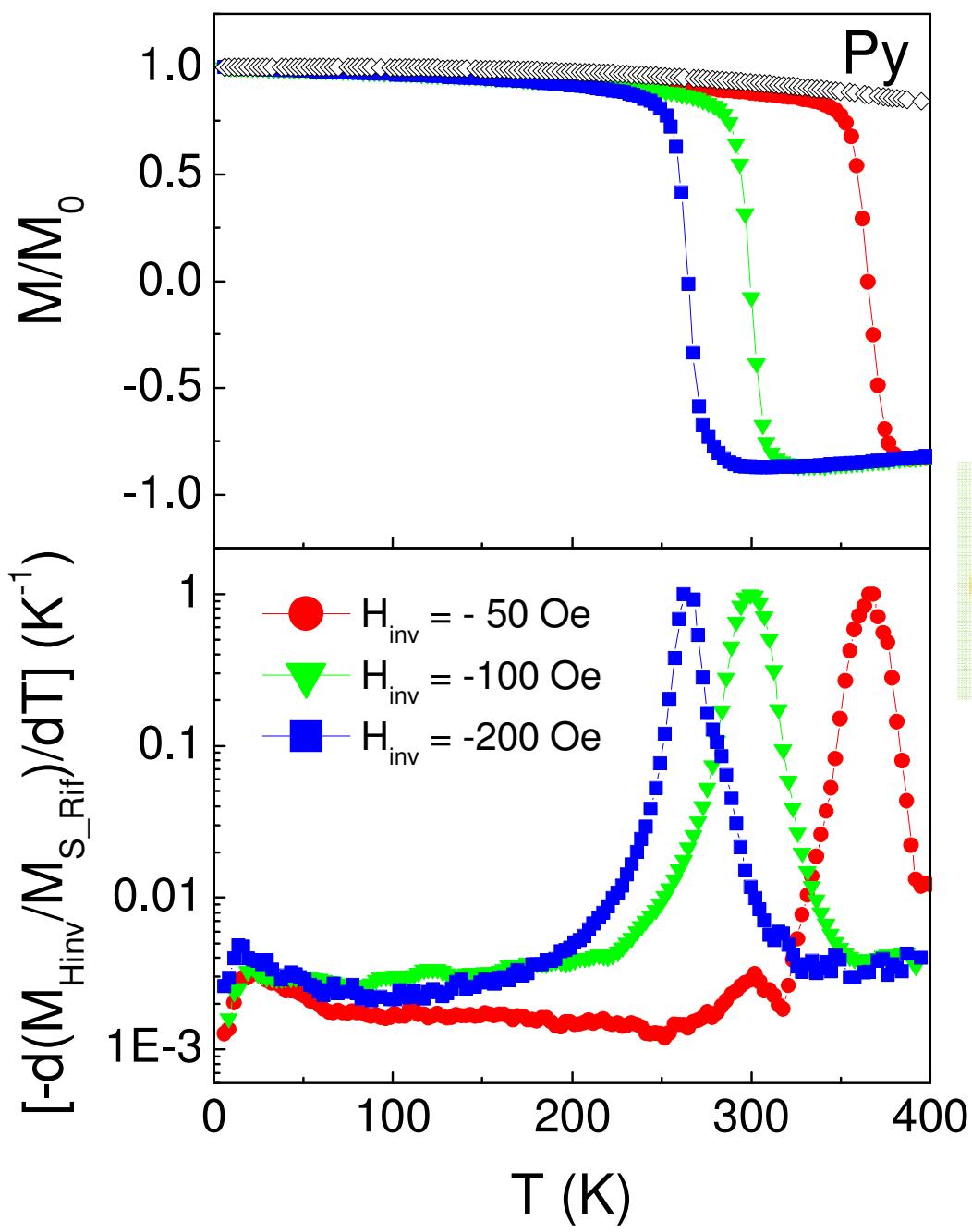


Change of magnetic  
regime at  $T \sim 100\text{ K}$

## Magnetization reversal study - SQUID measurement procedure







AFM film consists of non-interacting nanograins

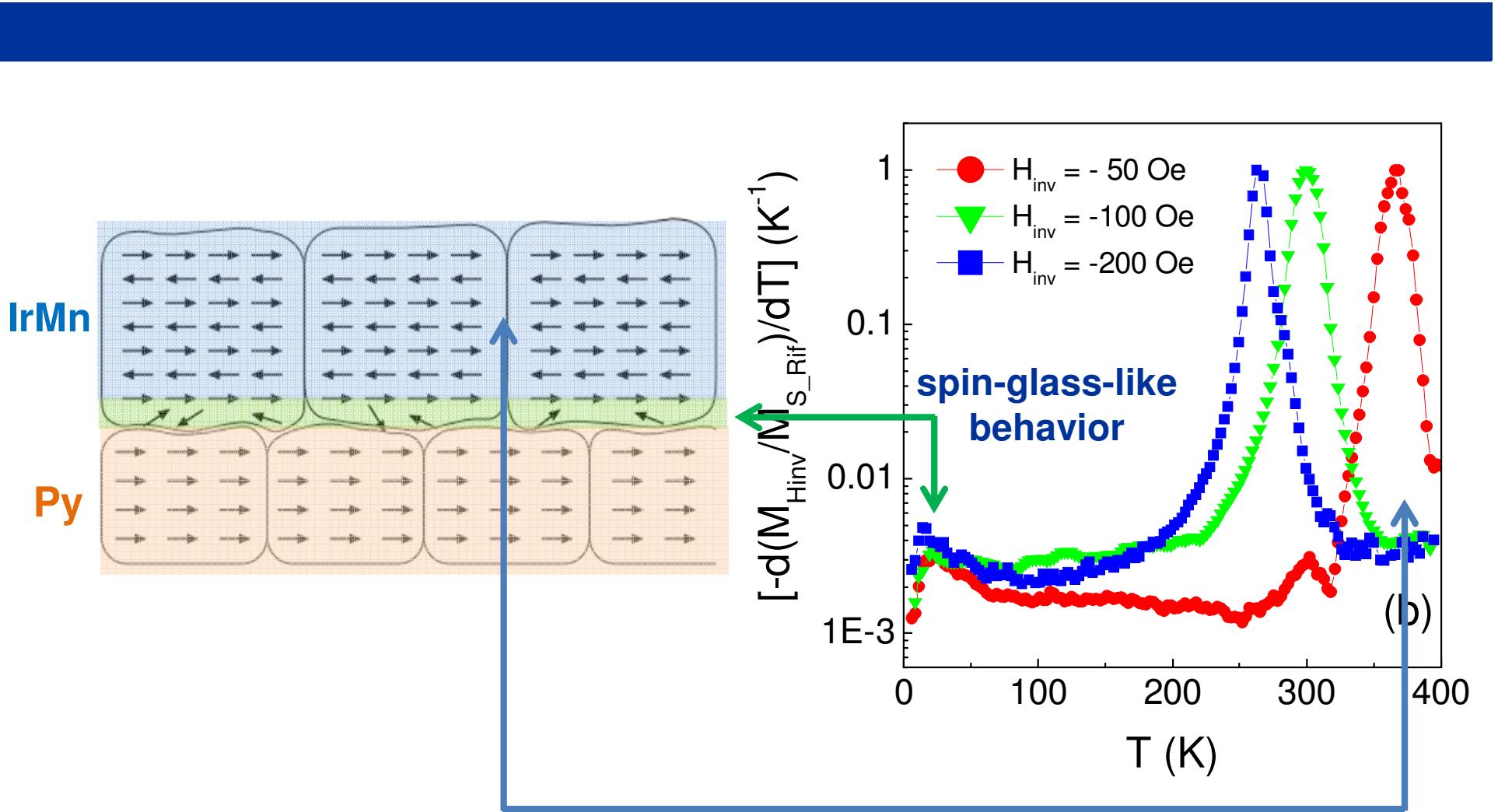


Distribution of effective anisotropy energy barriers  $\Delta E$

$$\left( \frac{M_{H_{\text{inv}}}}{M_{S_{\text{Rif}}}} + 1 \right) \propto \int_{\Delta E_{\text{crit}}}^{\infty} f(\Delta E) d\Delta E$$

We obtain information on the anisotropy energy barrier distribution of the AFM as it is felt by the FM component

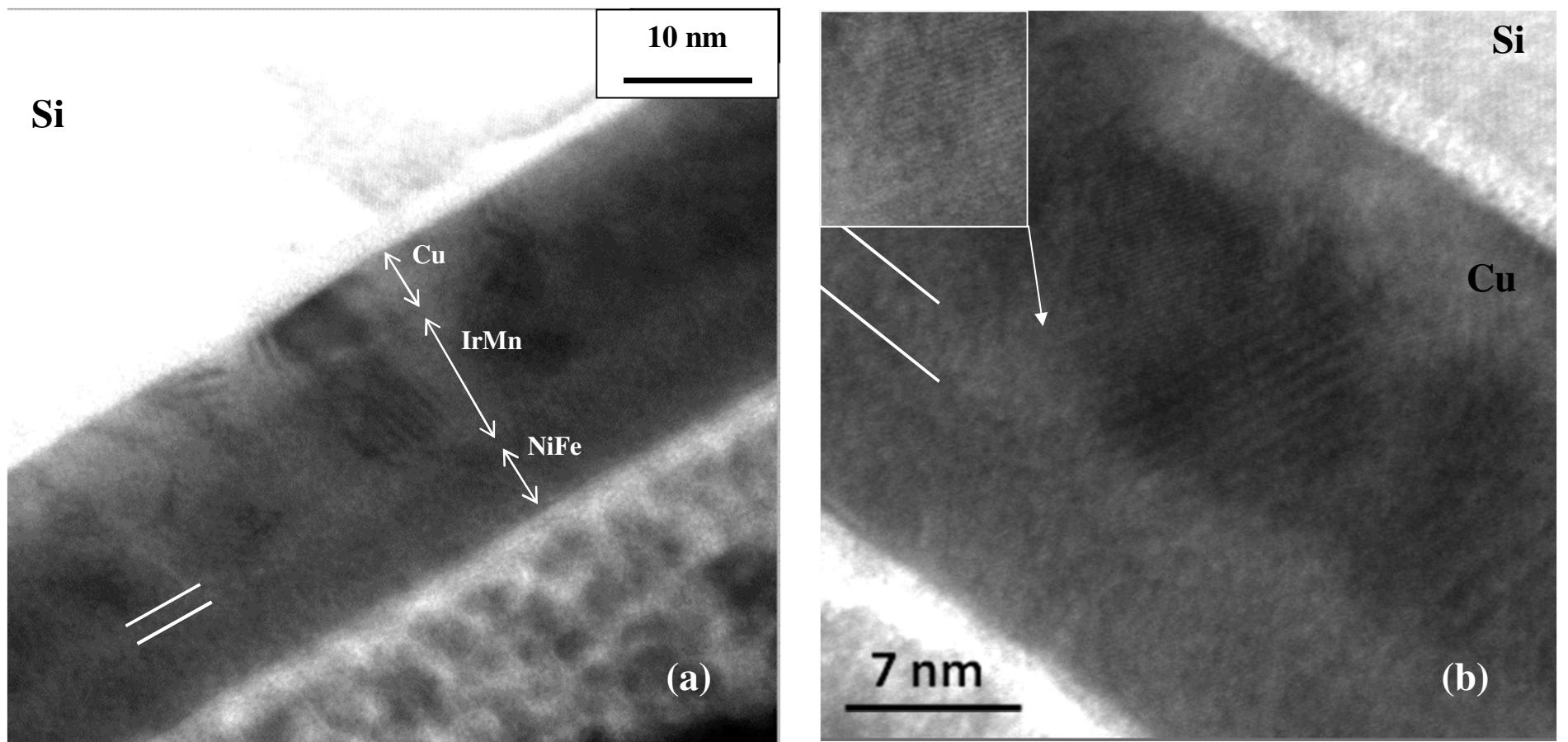
F. Spizzo et al., J. Phys.: Condens. Matter 25, 386001 (2013)



$$V = 25 kT_B / K_{\text{IrMn}}$$

$\Rightarrow$  size  $\sim 10 \text{ nm}$

$$K_{\text{IrMn}} = 1.8 \times 10^6 \text{ erg/cm}^3$$



Existence of a disordered AFM region at the interface with the NiFe phase

**TEM results confirm our prediction on the structure of the AFM phase**

## $T > 100$ K

Only the interfacial AFM spins tightly anchored to the spin lattice of the bulk AFM nanograins contribute to  $H_{ex}$

## $T \sim 100$ K

The frozen collective state breaks up.  
Polarizing action of bulk AFM spins on the interfacial ones prevents the development of a paramagnetic state.

### Re-entrant antiferromagnetism

## $T < 100$ K

AFM interfacial spins are frozen and subjected to a high effective anisotropy.

T  
↑

$H_{ex}$  decreases and finally the EB effect disappears

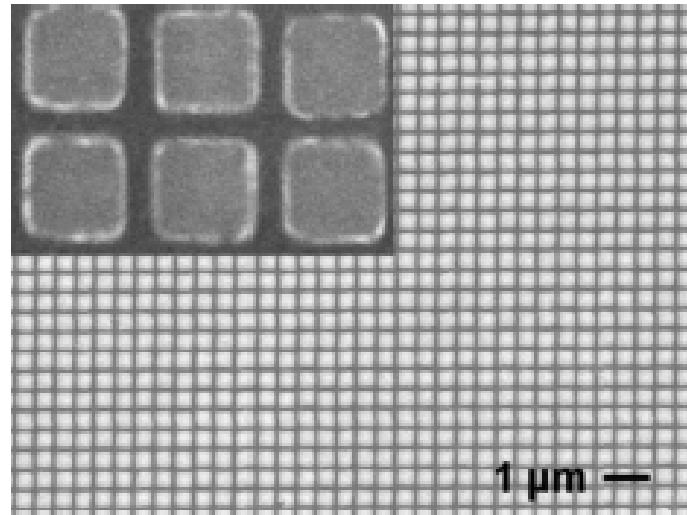
$H_{ex}$  is maximized

# From the continuous film to dot arrays

Si / Cu[5 nm] / **IrMn**[10 nm] / **Py** [5 nm]

Electron beam lithography  
and lift-off

dc-magnetron sputtering  
( $H_{dep} = 400$  Oe)



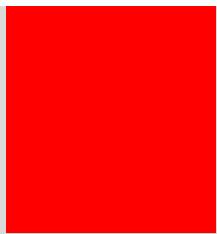
FM  
AFM



spatial confinement

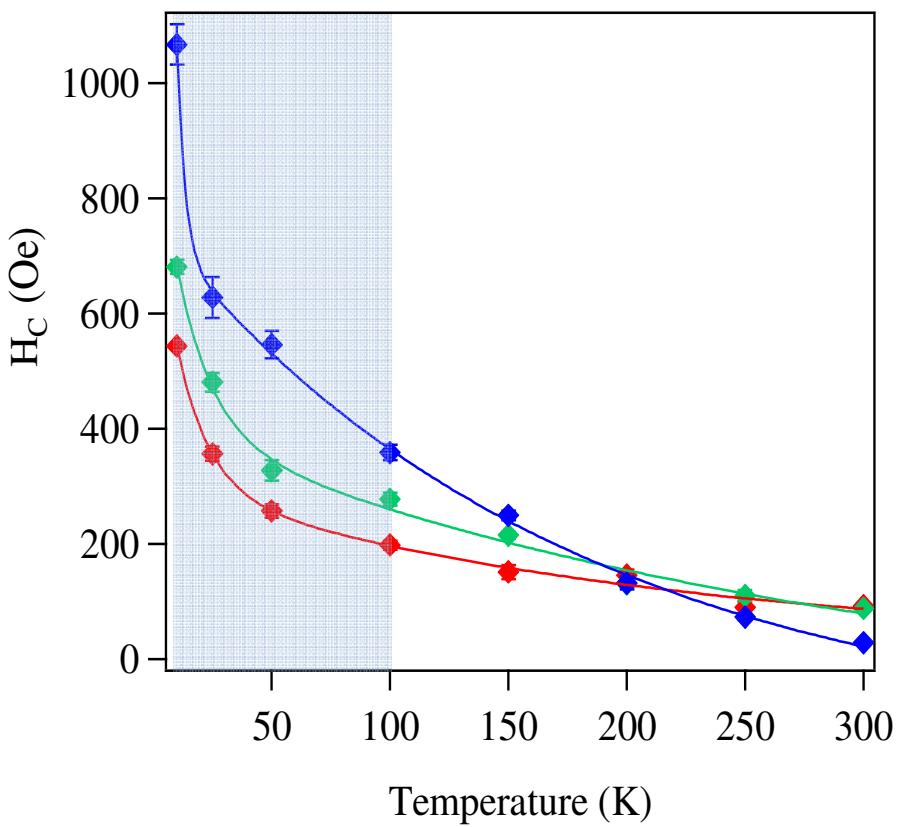
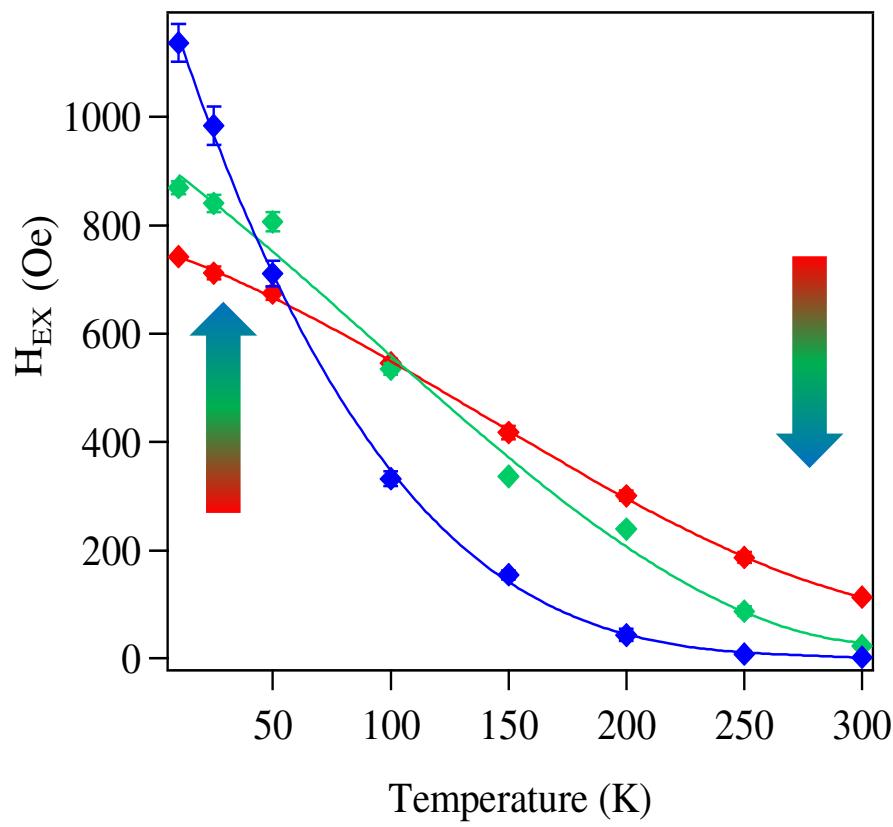
FM  
AFM

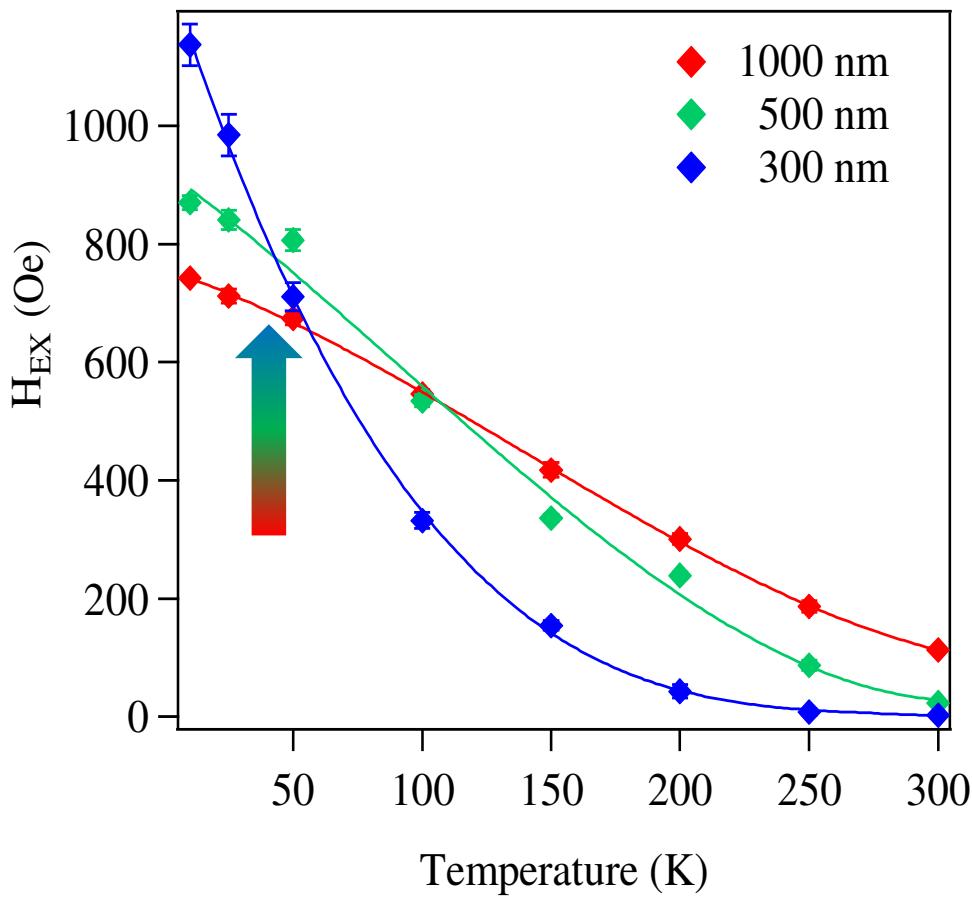




A = 1000 nm   B = 500 nm   C = 300 nm

**MOKE - FC hysteresis loops**  
( $H_{cool} = 500$  Oe;  
10-300 K temperature range)



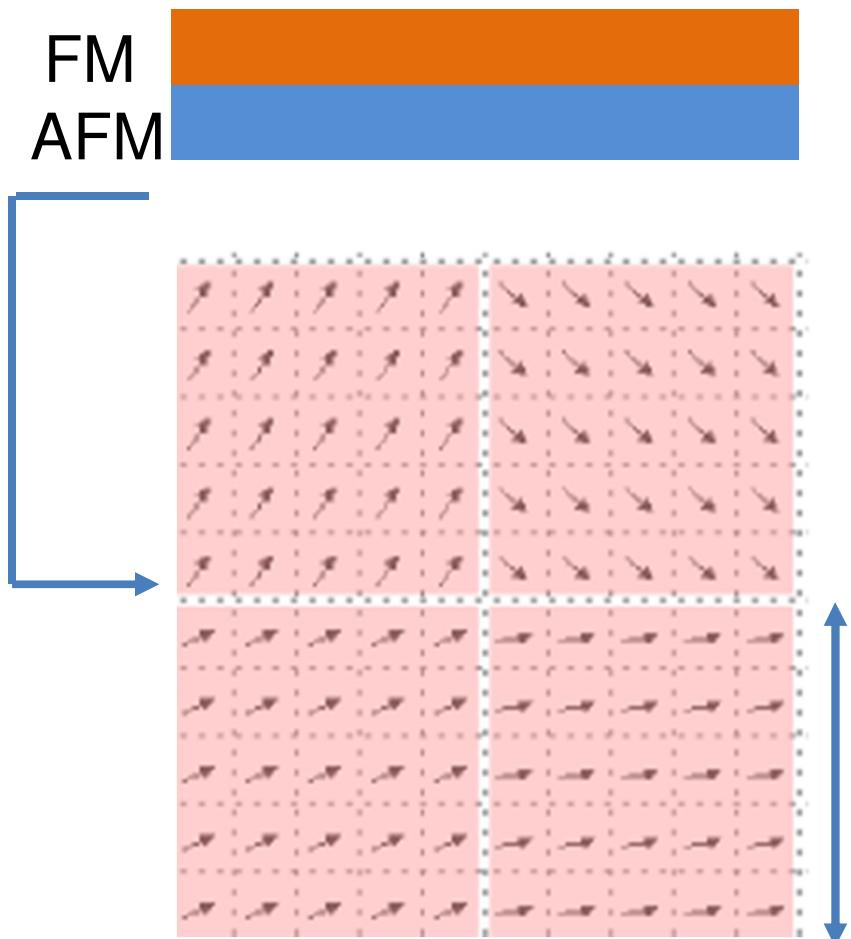


At low temperature

The correlation length among  
the AFM interfacial spins  
increases with reducing T



Object Oriented MicroMagnetic Framework



## Dependence of $H_{ex}$ on the AFM correlation length $\lambda$

Dot size = 1200 nm

OOMMF cell size = 10 nm

$K_{AFM} = 2 \times 10^7$  erg/cm<sup>3</sup> cells:

FM/AFM exchange interaction =  $10^{-7}$  erg/cm

**Different cell size:  
10, 20, 100, 200, 300 nm**

*F. Spizzo et al., Phys. Rev. B 91  
(2015) 064410*



Object Oriented MicroMagnetic Framework

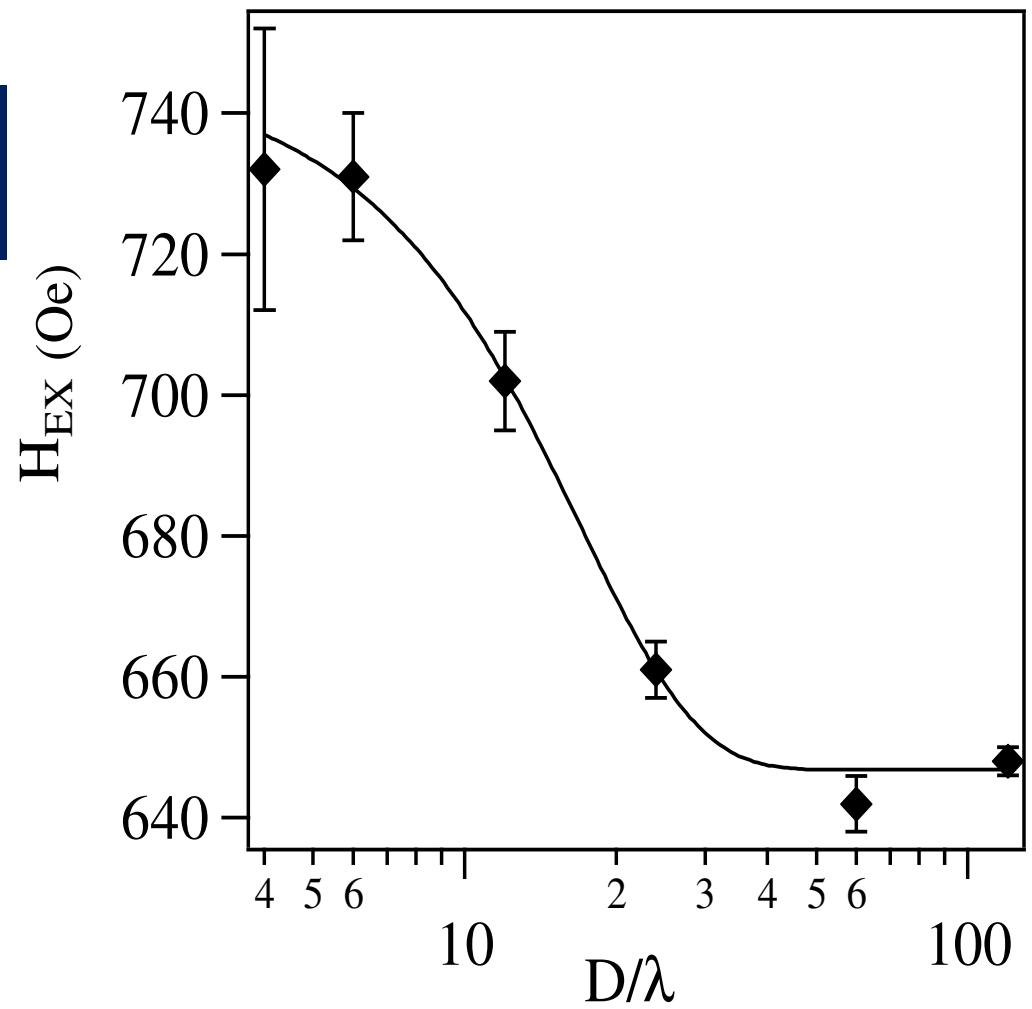
## Dependence of $H_{ex}$ on the AFM correlation length $\lambda$

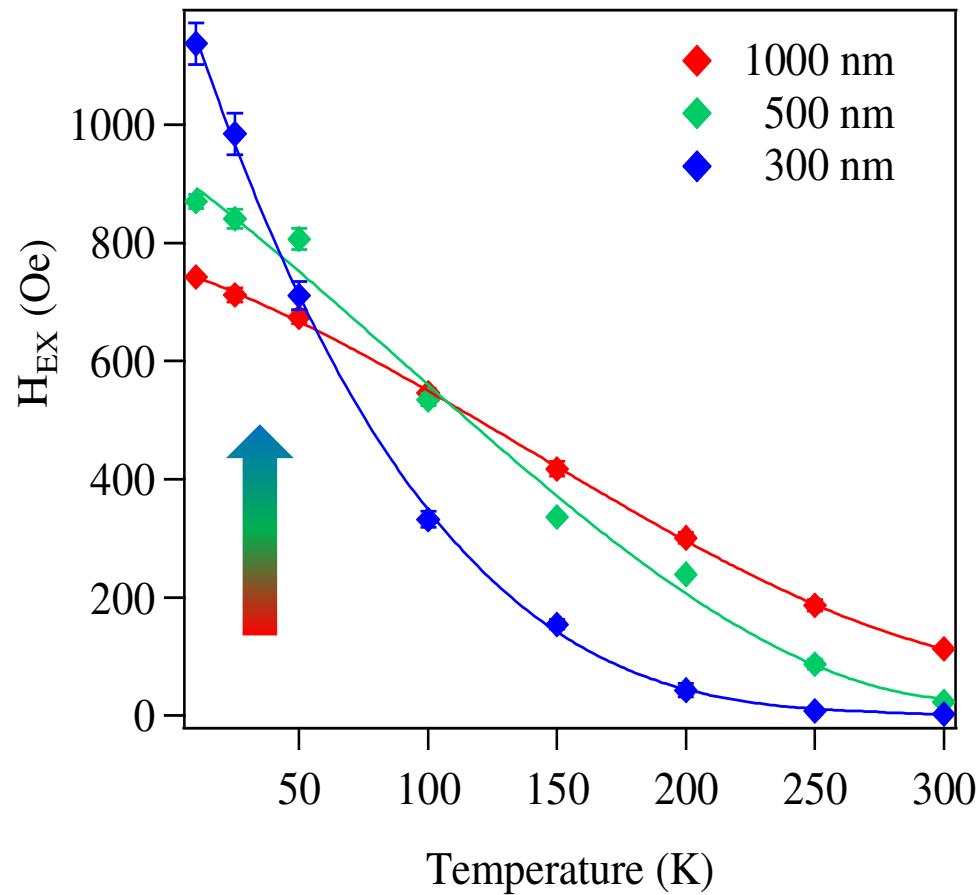
Dot size = 1200 nm

All the AFM cells with high K (100% pinning centers)

Different cell size:  
10, 20, 100, 200, 300 nm

$H_{ex}$  increases as  
 $D/\lambda \rightarrow 1$





At low temperature

Spin correlation effect

Correlated AFM spins exert a stronger pinning action as  
 $D/\lambda \rightarrow 1$

# Conclusions

**Re-entrant antiferromagnetism  $\Rightarrow$  Passage from the glassy to the AFM state**

- **Re-entrant magnetic regime:** the magnetism of AFM interfacial spins is sustained by stable nanograins.

## Exchange coupling mechanism

- **Low temperature:** collective freezing of the disordered AFM spins  $\Rightarrow$  high  $H_{\text{ex}}$ .
- **High temperature:** FM/AFM coupling governed by a fraction of interfacial AFM spins.
- **Spatial confinement**  $\Rightarrow$  spin correlation effect

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**Thanks for attention**